

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
85V	1.8mΩ@10V	275A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

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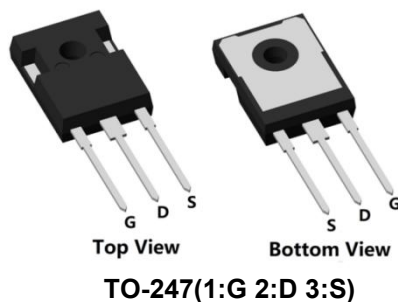
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

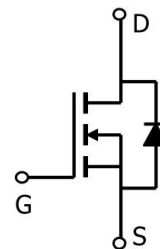
Applications

- Power switching application
- DC-DC Converter
- Power Management

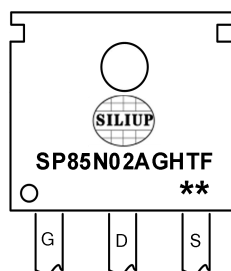
Package



Circuit diagram



Marking



SP85N02AGHTF : Product code
** : Week code

Order Information

Device	Package	Unit/Tube
SP85N02AGHTF	TO-247	30

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	85	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	Silicon limit	I_D	310	A
Continuous Drain Current (Tc=25°C)	Package limit	I_D	275	A
Continuous Drain Current (Tc=100°C)		I_D	183	A
Pulsed Drain Current		I_{DM}	1100	A
Single Pulse Avalanche Energy ¹		E_{AS}	1650	mJ
Power Dissipation (Tc=25°C)		P_D	270	W
Power Dissipation (Tc=100°C)		P_D	108	W
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	0.46	°C/W
Storage Temperature Range		T_{STG}	-55 to 150	°C
Operating Junction Temperature Range		T_J	-55 to 150	°C

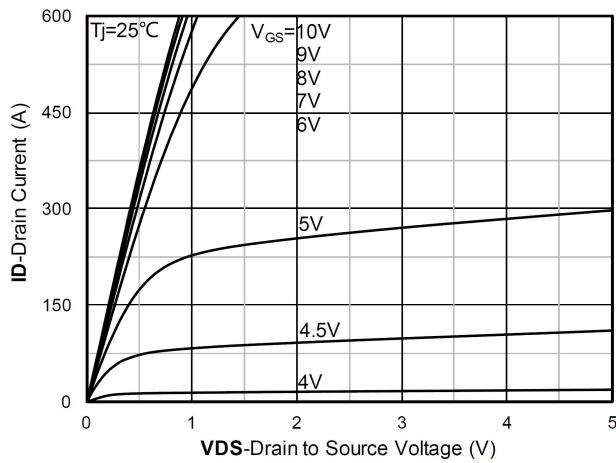
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	85	-	-	V
Drain Cut-Off Current	IDSS	VDS=68V , VGS=0V , TJ=25℃	-	-	1	μA
Gate Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	2.6	3.0	3.4	V
Drain-Source ON Resistance	RDS(ON)	VGS=10V , ID=20A	-	1.8	2.2	mΩ
Gate Resistance	RG	VDS=40V , VGS=0V , f=1MHz	-	2.2	-	Ω
Dynamic Characteristics						
Input Capacitance	Ciss	VDS=40V , VGS=0V , f=1MHz	-	9222	-	pF
Output Capacitance	Coss		-	3200	-	
Reverse Transfer Capacitance	Crss		-	84	-	
Total Gate Charge	Qg	VDS=40V , VGS=10V , ID=165A	-	145	-	nC
Gate-Source Charge	Qgs		-	51	-	
Gate-Drain Charge	Qgd		-	25	-	
Gate Plateau Voltage	Vplateau		-	4.5	-	
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=40V, VGS=10V , RG=1.6Ω, ID=165A	-	27	-	nS
Rise Time	tr		-	75	-	
Turn-Off Delay Time	td(off)		-	86	-	
Fall Time	tf		-	35	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	VSD	IS = 1A, VGS = 0V	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	275	A
Reverse Recovery Time	Trr	IS=50A , di/dt=100A/us , TJ=25℃	-	106	-	nS
Reverse Recovery Charge	Qrr		-	256	-	nC

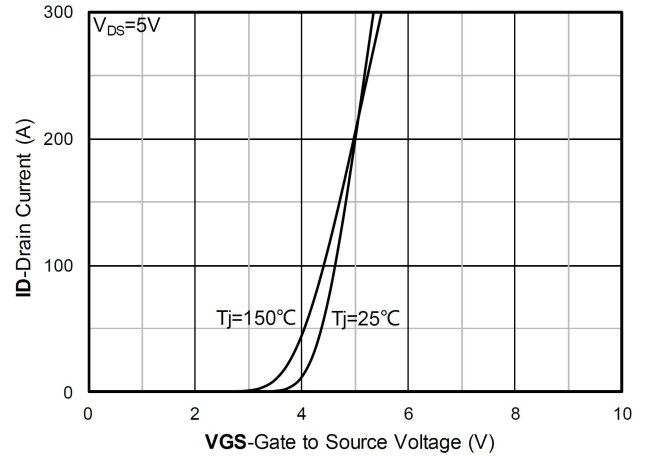
Note :

1. The test condition is $V_{DD}=45V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$;

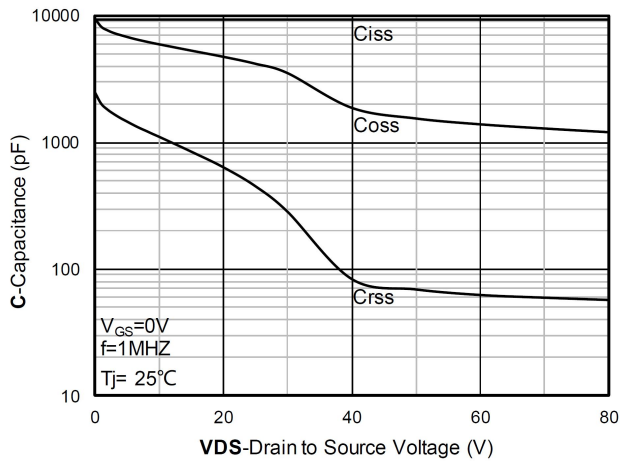
Typical Characteristics



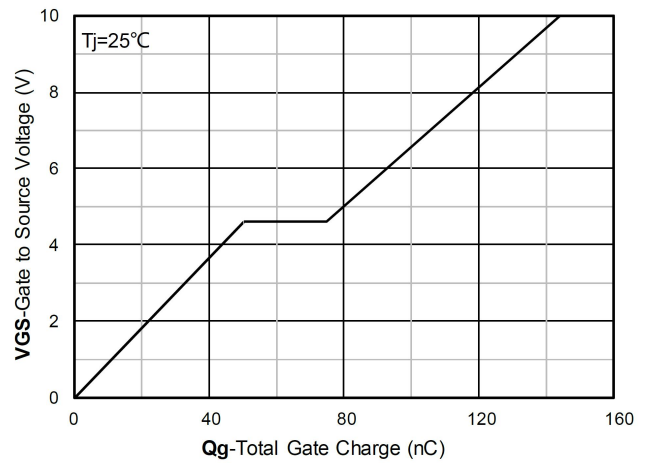
Output Characteristics



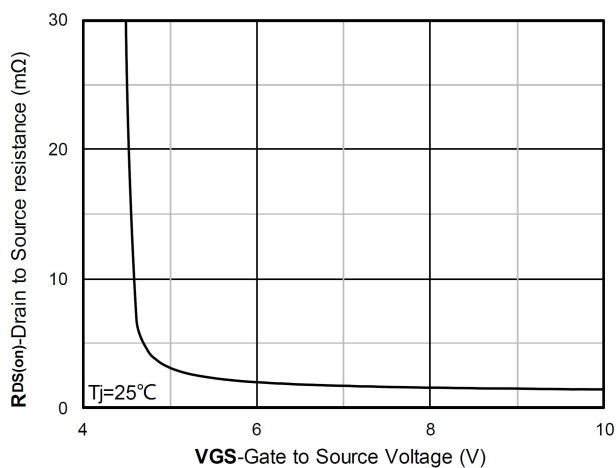
Transfer Characteristics



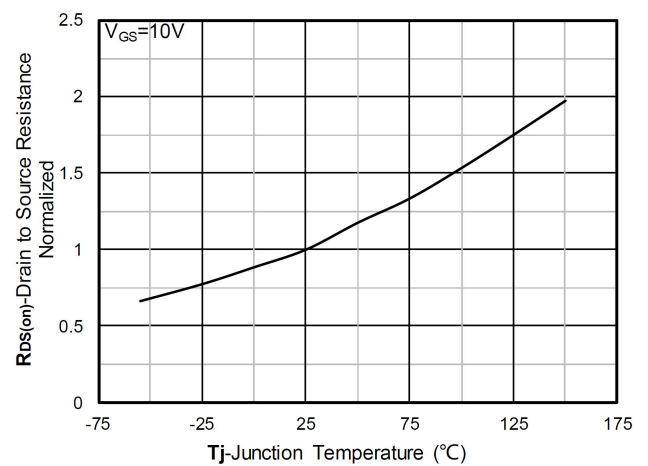
Capacitance Characteristics



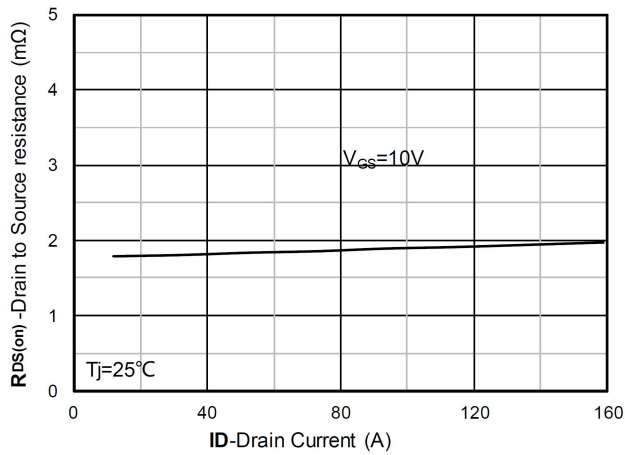
Gate Charge



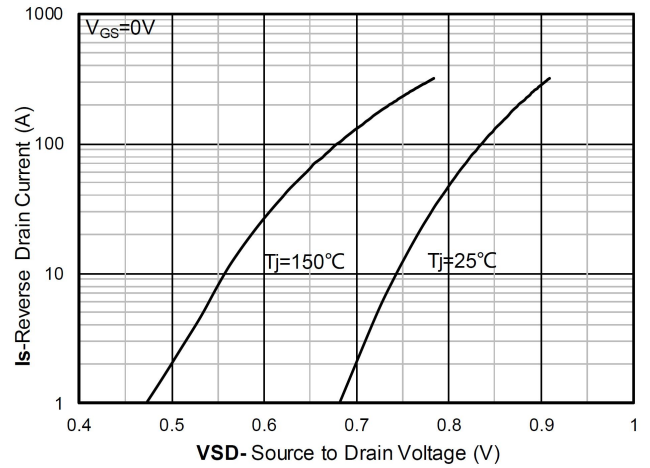
On-Resistance vs. Gate to Source Voltage



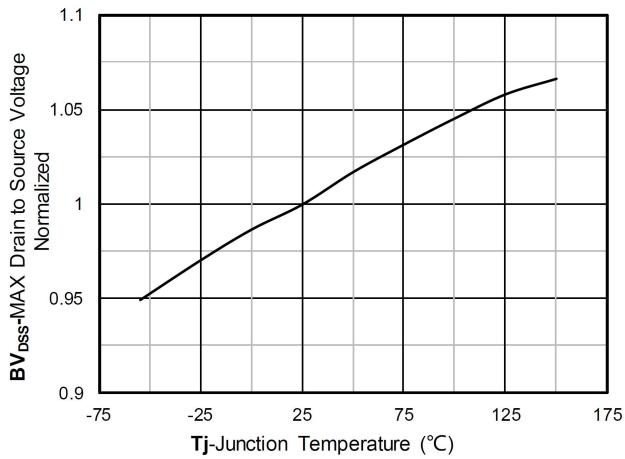
Normalized On-Resistance



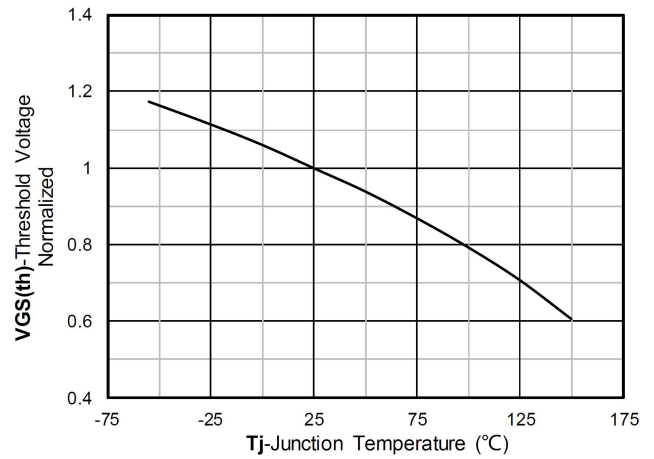
$R_{DS(on)}$ vs. Drain Current



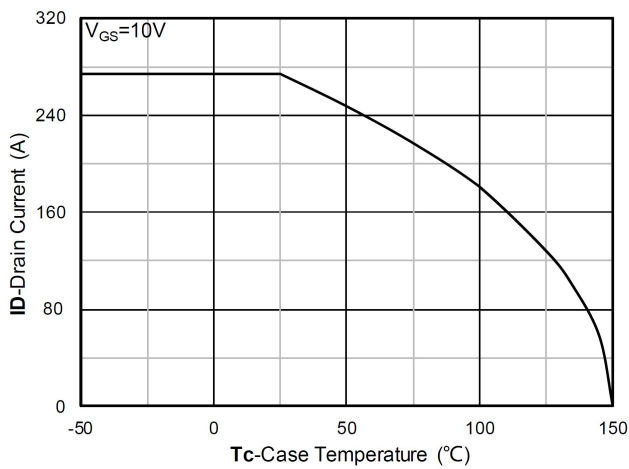
Forward characteristics of reverse diode



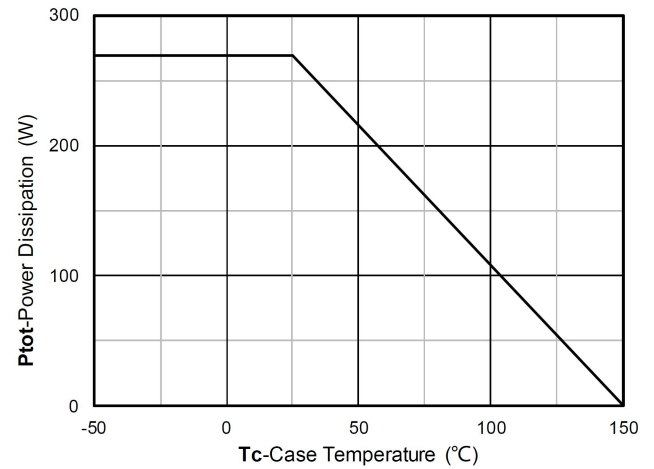
Normalized breakdown voltage



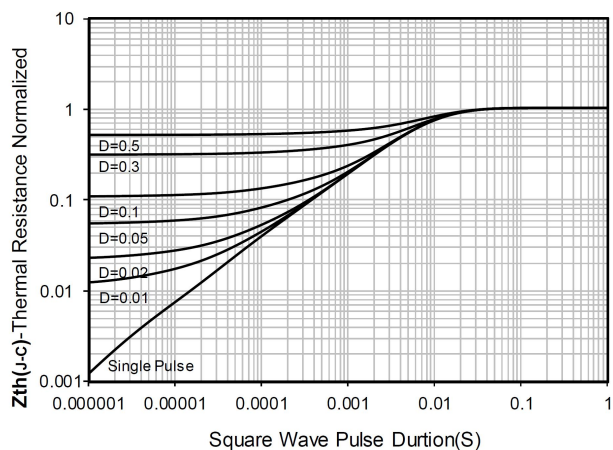
Normalized Threshold voltage



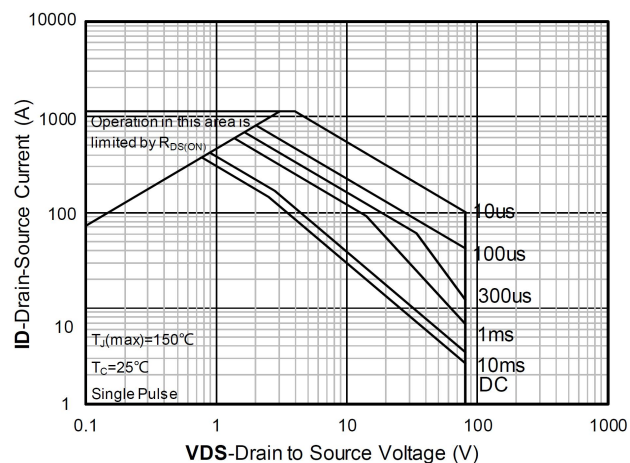
Current dissipation



Power dissipation



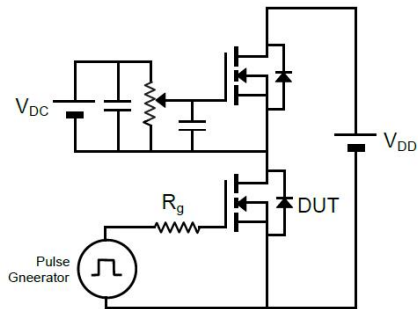
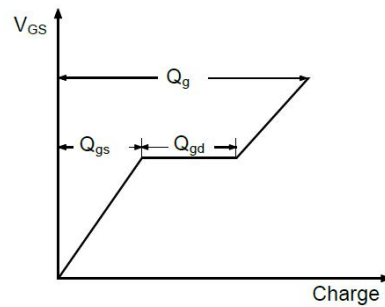
Normalized Maximum Transient Thermal Impedance



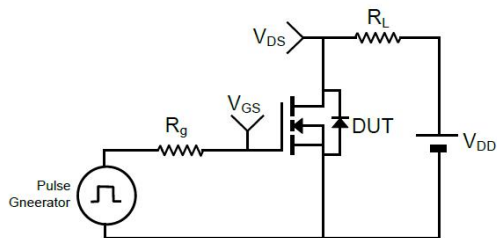
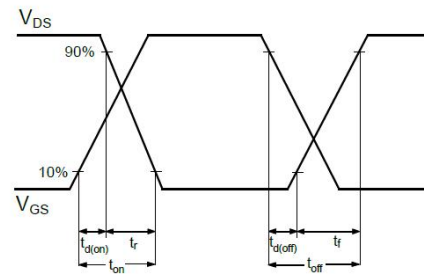
Safe Operation Area

Test Circuit

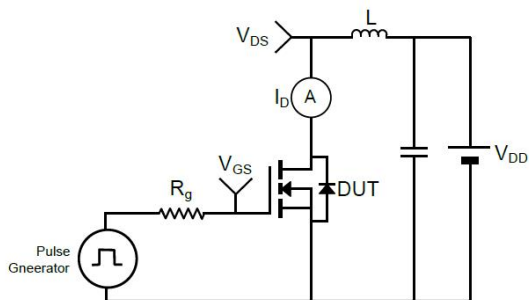
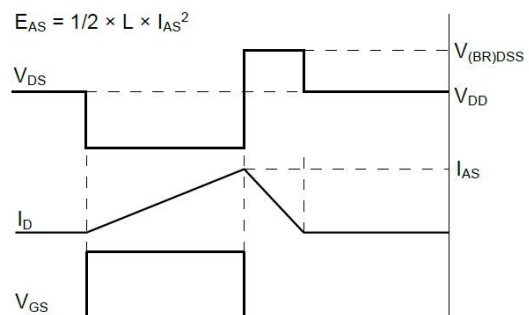
Gate Charge



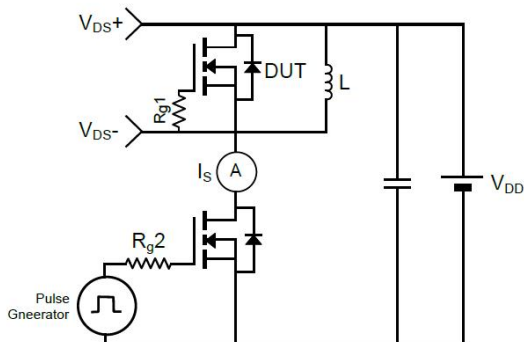
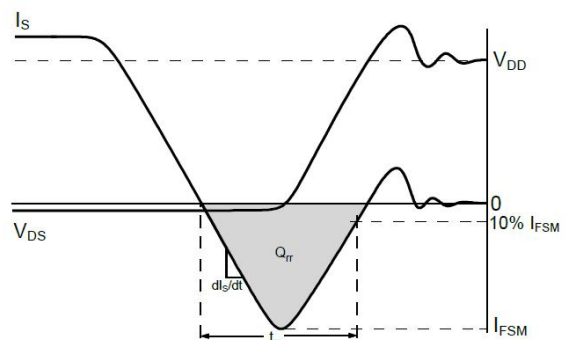
Resistive Load Switching Time

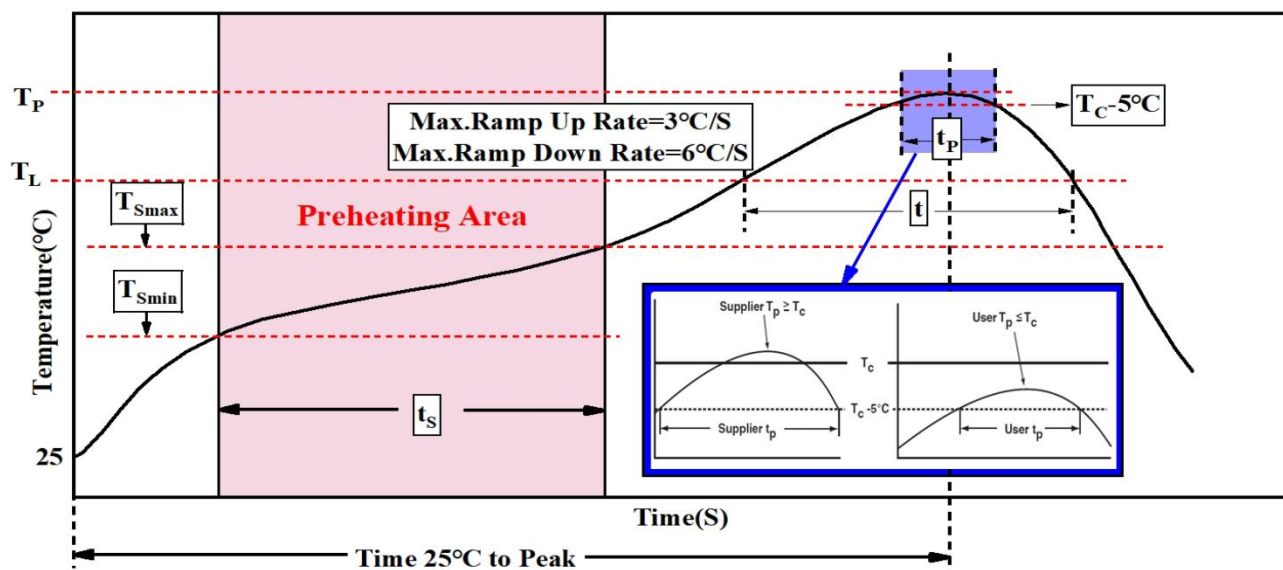


Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering(Pb-Free)


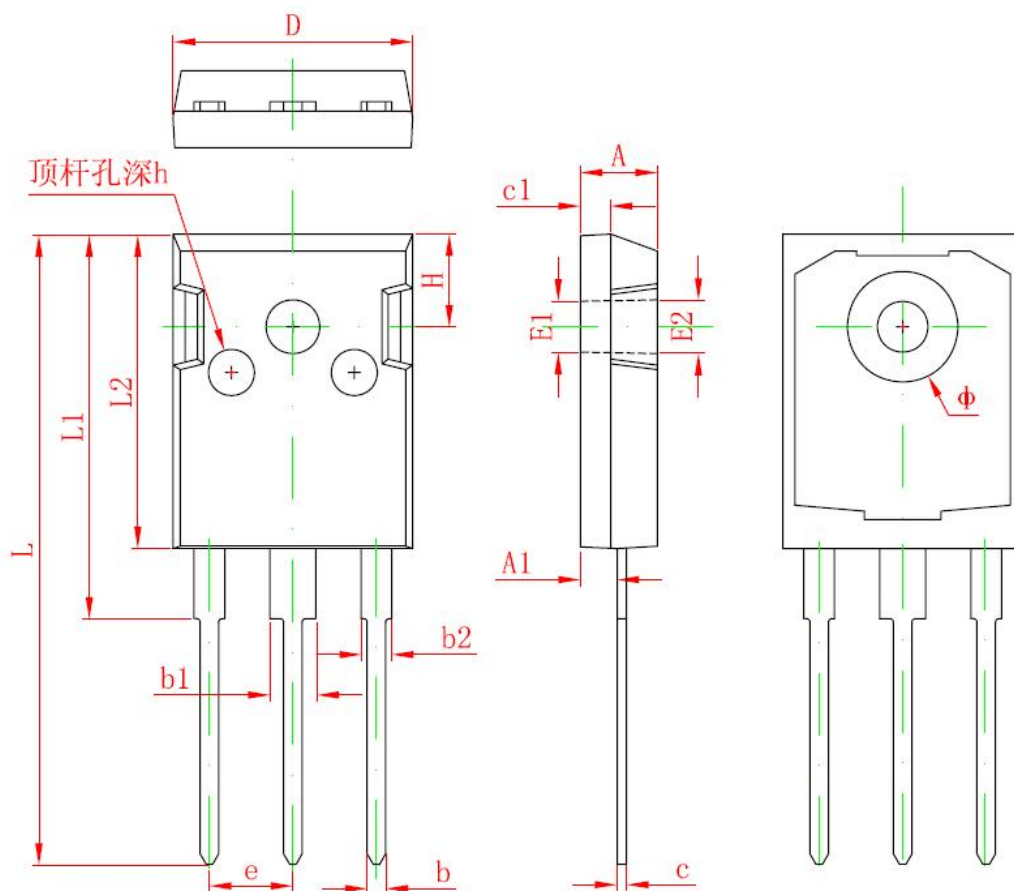
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{Smin})	100°C	150°C
Temperature max (T_{Smax})	150°C	200°C
Time (T_{Smin} to T_{Smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{Smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217°C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T_P)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_C)	20** seconds	30** seconds
Average ramp-down rate (T_P to T_{Smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_P) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_P) is defined as a supplier minimum and a user maximum		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

TO-247 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.700	5.300
A1	2.100	2.600
b	1.000	1.400
b1	2.800	3.200
b2	1.800	2.200
c	0.500	0.700
c1	1.900	2.500
D	15.450	16.200
E1	3.500 REF.	
E2	3.600 REF.	
L	40.400	41.600
L1	24.750	25.750
L2	20.300	21.300
Φ	7.100	7.300
e	5.450 TYP.	
H	5.980 REF.	
h	0.000	0.300